

P-Channel Enhancement Mode MOSFET

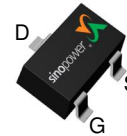
Features

- 30V/-4.8A,
 $R_{DS(ON)} = 56m\Omega$ (Max.) @ $V_{GS} = -10V$
 $R_{DS(ON)} = 68m\Omega$ (Max.) @ $V_{GS} = -4.5V$
 $R_{DS(ON)} = 94m\Omega$ (Max.) @ $V_{GS} = -2.5V$
- Super High Dense Cell Design
- Reliable and Rugged
- Lead Free and Green Devices Available
(RoHS Compliant)

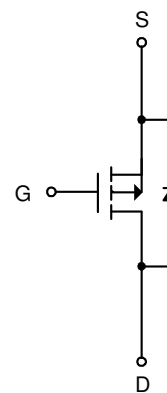
Applications

- Power Management in Notebook Computer,
Portable Equipment and Battery Powered
Systems.

Pin Description

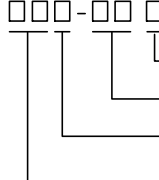


Top View of SOT-23N



P-Channel MOSFET

Ordering and Marking Information

SM2421PS □□□-□□□  Assembly Material Handling Code Temperature Range Package Code	Package Code AN : SOT-23N Operating Junction Temperature Range C : -55 to 150 °C Handling Code TR : Tape & Reel (3000ea/reel) Assembly Material G : Halogen and Lead Free Device
SM2421PS AN : B21XX	XX - Lot Code

Note : SINOPOWER lead-free products contain molding compounds/die attach materials and 100% matte tin plate termination finish; which are fully compliant with RoHS. SINOPOWER lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J-STD-020D for MSL classification at lead-free peak reflow temperature. SINOPOWER defines "Green" to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

SINOPOWER reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter		Rating	Unit
V_{DSS}	Drain-Source Voltage		-30	V
V_{GSS}	Gate-Source Voltage		± 12	
I_D^*	Continuous Drain Current	$T_A = 25^\circ\text{C}$	-4.8	A
		$T_A = 70^\circ\text{C}$	-3.8	
I_{DM}^*	300 μs Pulsed Drain Current	$T_A = 25^\circ\text{C}$	-19	
		$T_A = 70^\circ\text{C}$	-15	
I_S^*	Diode Continuous Forward Current		-1	$^\circ\text{C}$
T_J	Maximum Junction Temperature		150	
T_{STG}	Storage Temperature Range		-55 to 150	
P_D^*	Maximum Power Dissipation	$T_A = 25^\circ\text{C}$	1.9	W
		$T_A = 70^\circ\text{C}$	1.2	
$R_{\theta JA}^*$	Thermal Resistance-Junction to Ambient	$t \leq 10\text{s}$	65	$^\circ\text{C/W}$
		Steady state	120	
$R_{\theta JL}$	Thermal Resistance-Junction to Lead	Steady state	52	

Note : *Surface Mounted on 1in² pad area, $t \leq 10\text{sec}$.

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$, $I_{DS}=-250\mu\text{A}$	-30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-24\text{V}$, $V_{GS}=0\text{V}$	-	-	-1	μA
		$T_J=85^\circ\text{C}$	-	-	-30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_{DS}=-250\mu\text{A}$	-0.5	-0.9	-1.3	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 12\text{V}$, $V_{DS}=0\text{V}$	-	-	± 100	nA
$R_{DS(ON)}^a$	Drain-Source On-State Resistance	$V_{GS}=-10\text{V}$, $I_{DS}=-4.8\text{A}$	-	47	56	m Ω
		$V_{GS}=-4.5\text{V}$, $I_{DS}=-3.8\text{A}$	-	54	68	
		$V_{GS}=-2.5\text{V}$, $I_{DS}=-3\text{A}$	-	70	94	
V_{SD}^a	Diode Forward Voltage	$I_{SD}=-1\text{A}$, $V_{GS}=0\text{V}$	-	-0.7	-1	V
Gate Charge Characteristics^b						
Q_g	Total Gate Charge	$V_{DS}=-15\text{V}$, $V_{GS}=-10\text{V}$, $I_{DS}=-4.8\text{A}$	-	13.6	-	nC
Q_{gs}	Gate-Source Charge		-	1.2	-	
Q_{gd}	Gate-Drain Charge		-	2.0	-	

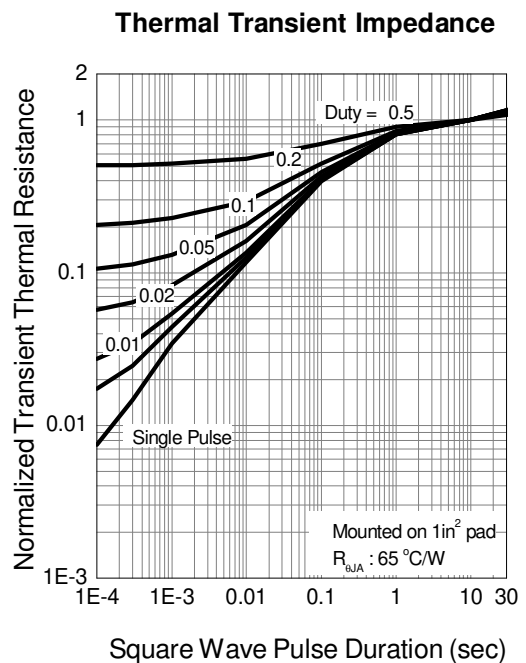
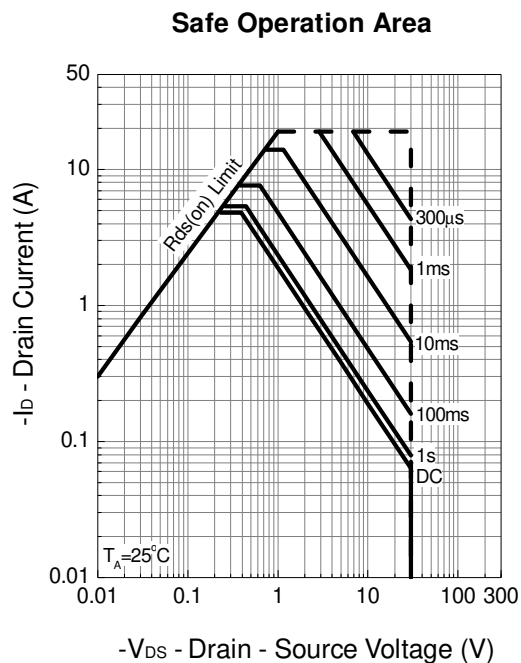
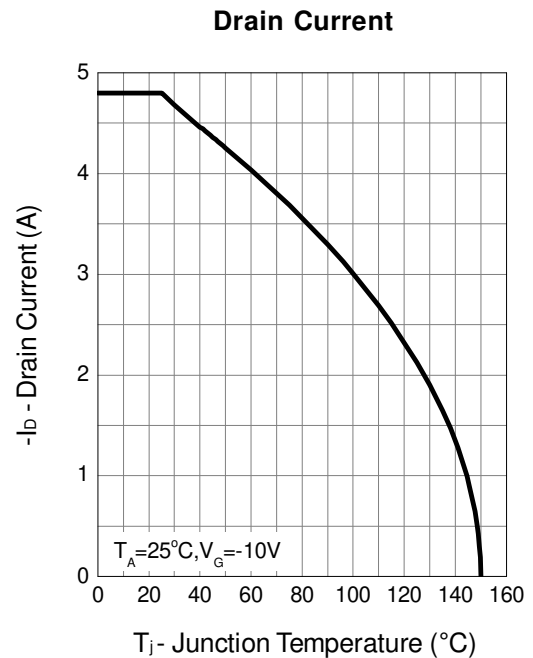
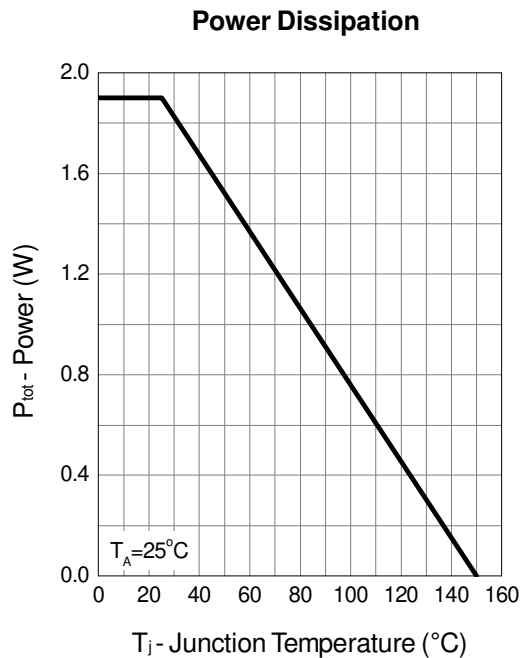
Electrical Characteristics (Cont.) ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Dynamic Characteristics^b						
R_G	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$	-	3.6	-	Ω
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=-15V,$ Frequency=1.0MHz	-	573	-	pF
C_{oss}	Output Capacitance		-	74	-	
C_{rss}	Reverse Transfer Capacitance		-	53	-	
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD}=-15V, R_L=10\Omega,$ $I_{DS}=-1A, V_{GEN}=-10V,$ $R_G=6\Omega$	-	6.9	-	ns
t_r	Turn-on Rise Time		-	12.3	-	
$t_{d(OFF)}$	Turn-off Delay Time		-	25	-	
t_f	Turn-off Fall Time		-	13	-	
t_{rr}	Reverse Recovery Time	$I_F=-4.8A, di_{SD}/dt = 100A/\mu s$	-	16	-	ns
Q_{rr}	Reverse Recovery Charge		-	11	-	nC

Note a : Pulse test ; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

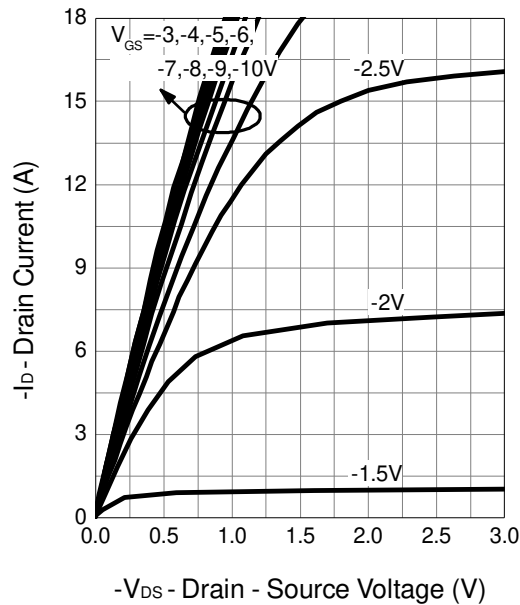
Note b : Guaranteed by design, not subject to production testing.

Typical Operating Characteristics

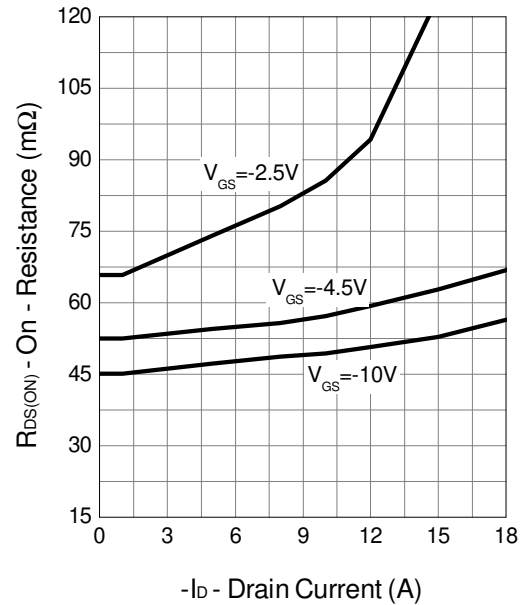


Typical Operating Characteristics (Cont.)

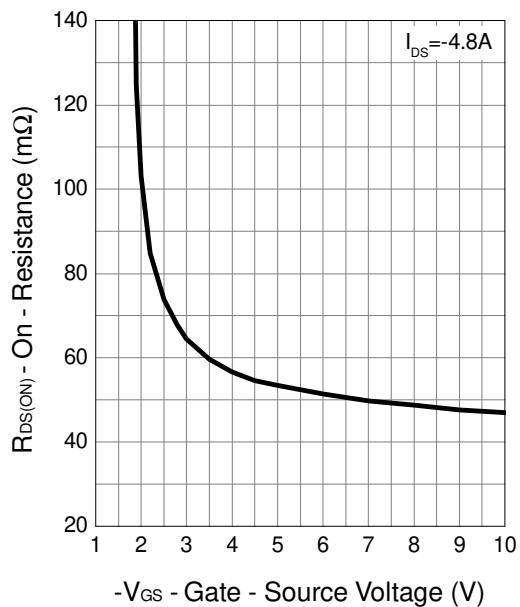
Output Characteristics



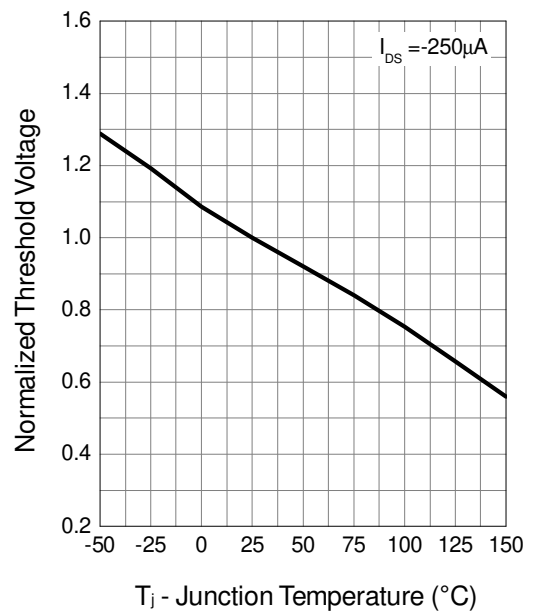
Drain-Source On Resistance



Gate-Source On Resistance

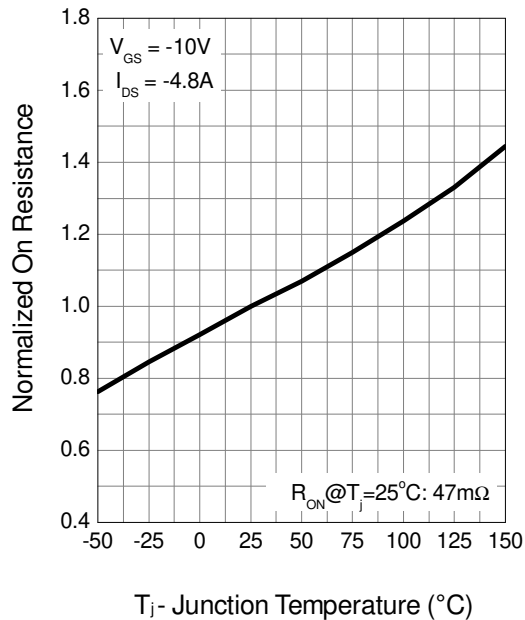


Gate Threshold Voltage

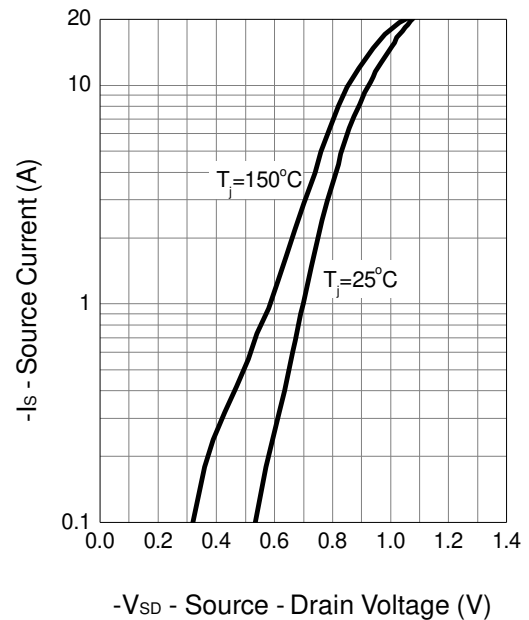


Typical Operating Characteristics (Cont.)

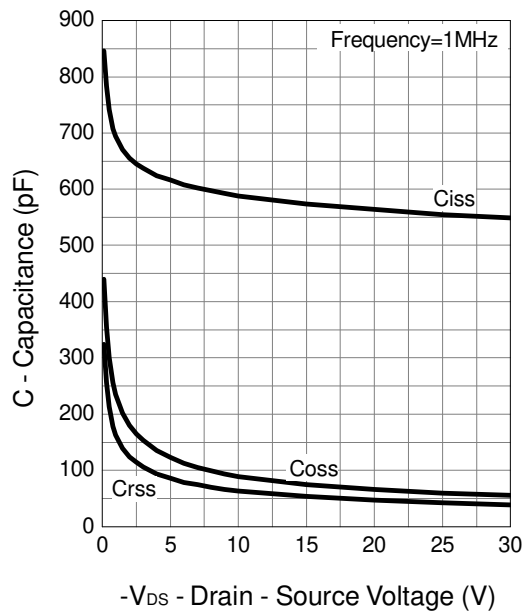
Drain-Source On Resistance



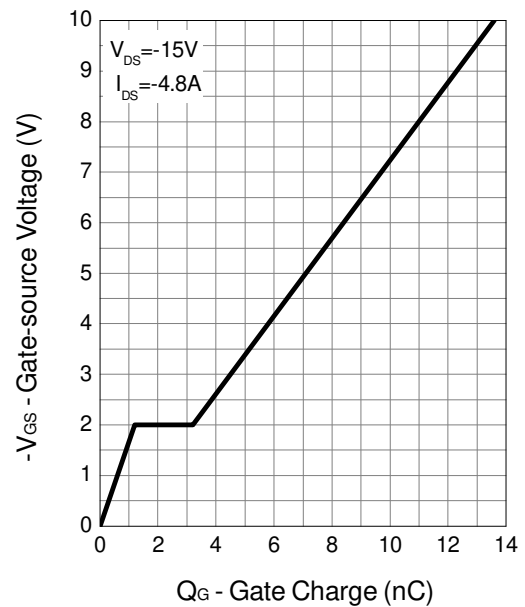
Source-Drain Diode Forward



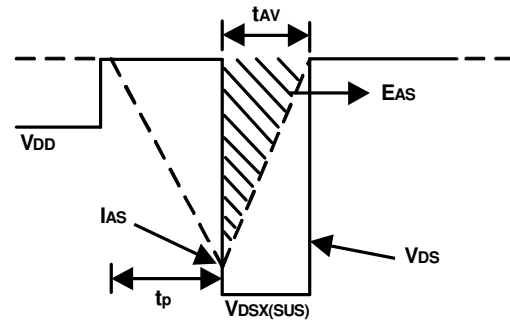
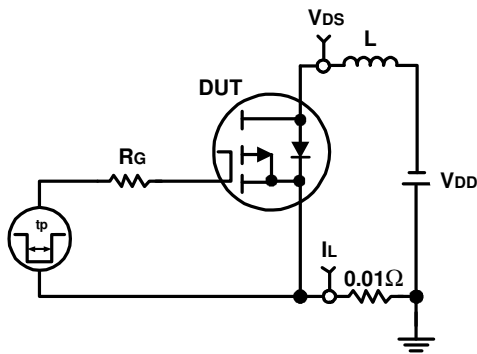
Capacitance



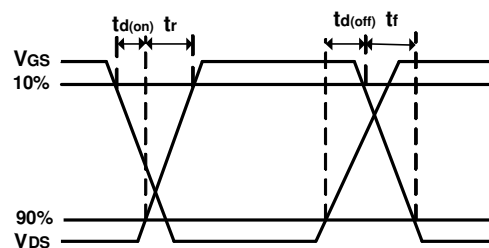
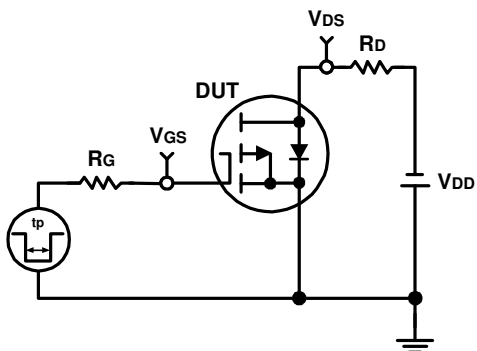
Gate Charge



Avalanche Test Circuit and Waveforms

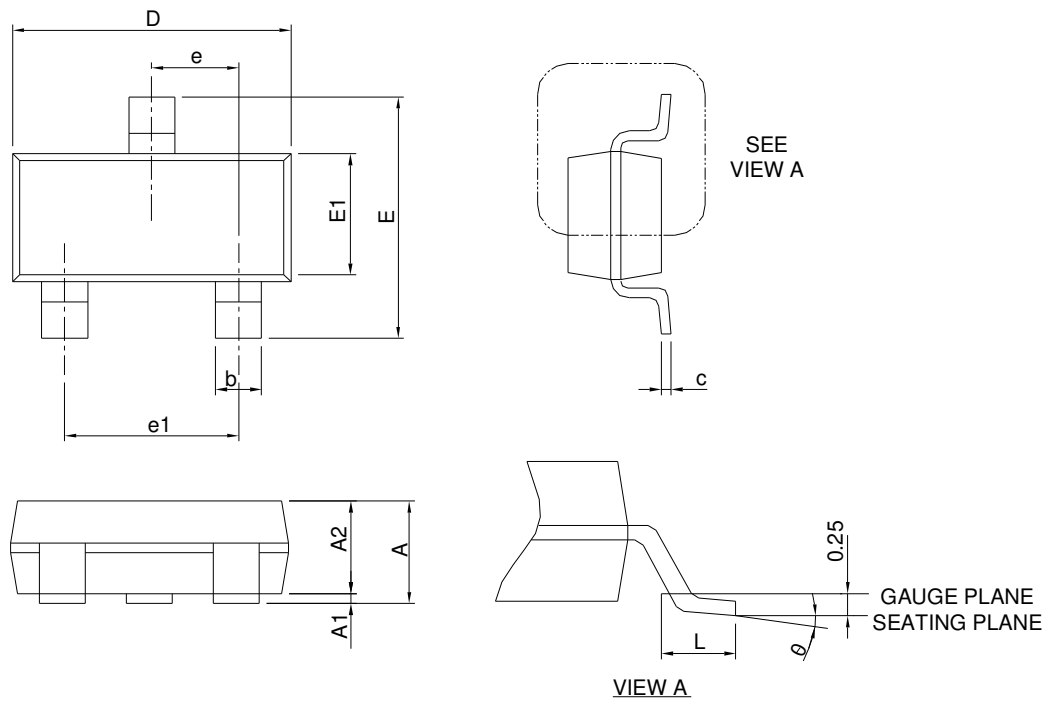


Switching Time Test Circuit and Waveforms



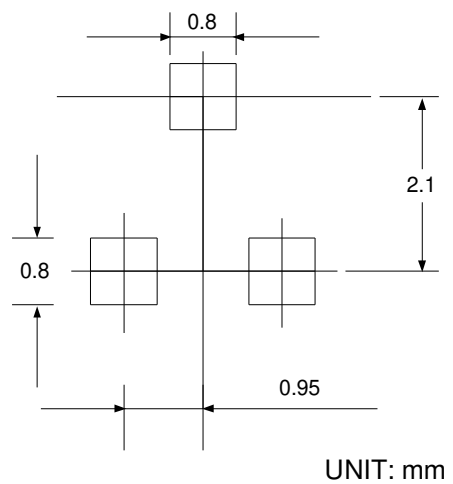
Package Information

SOT-23N



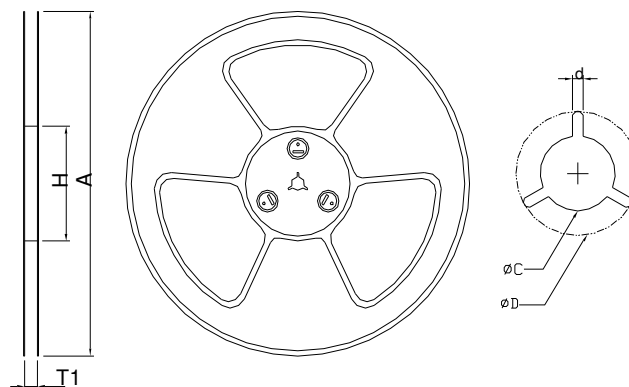
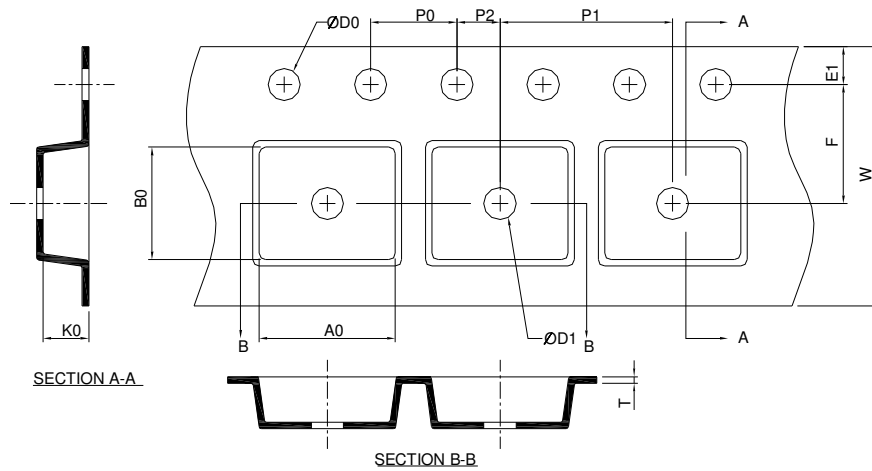
SYMBOL	SOT-23N			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	-	1.20	-	0.047
A1	0.00	0.10	0.000	0.004
A2	0.90	1.10	0.035	0.043
b	0.30	0.50	0.012	0.020
c	0.08	0.22	0.003	0.009
D	2.70	3.10	0.106	0.122
E	2.20	2.60	0.086	0.102
E1	1.20	1.40	0.047	0.055
e	0.95 BSC		0.037 BSC	
e1	1.90 BSC		0.075 BSC	
L	0.30	0.60	0.012	0.024
θ	0 °	8 °	0 °	8 °

RECOMMENDED LAND PATTERN



Note : Dimension D and E1 do not include mold flash, protrusions or gate burrs. Mold flash, protrusion or gate burrs shall not exceed 10 mil per side.

Carrier Tape & Reel Dimensions

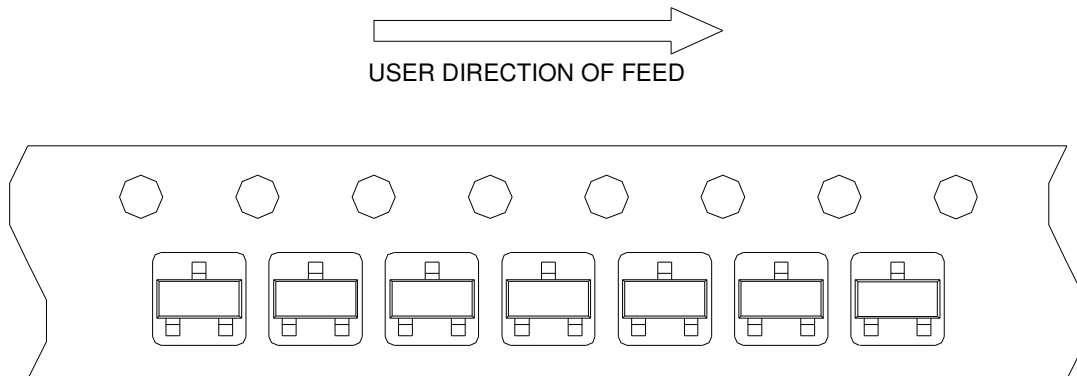


Application	A	H	T1	C	d	D	W	E1	F
SOT-23N	178.0±2.00	50 MIN.	9.4+2.00 -0.00	6.5+0.50 -0.20	1.5 MIN.	20.2 MIN.	8.0±0.30	1.75±0.10	3.5±0.05
	P0	P1	P2	D0	D1	T	A0	B0	K0
	4.0±0.10	4.0±0.10	2.0±0.05	1.5+0.10 -0.00	1.0 MIN.	0.6+0.00 -0.40	3.20±0.20	2.77±0.20	1.35±0.20

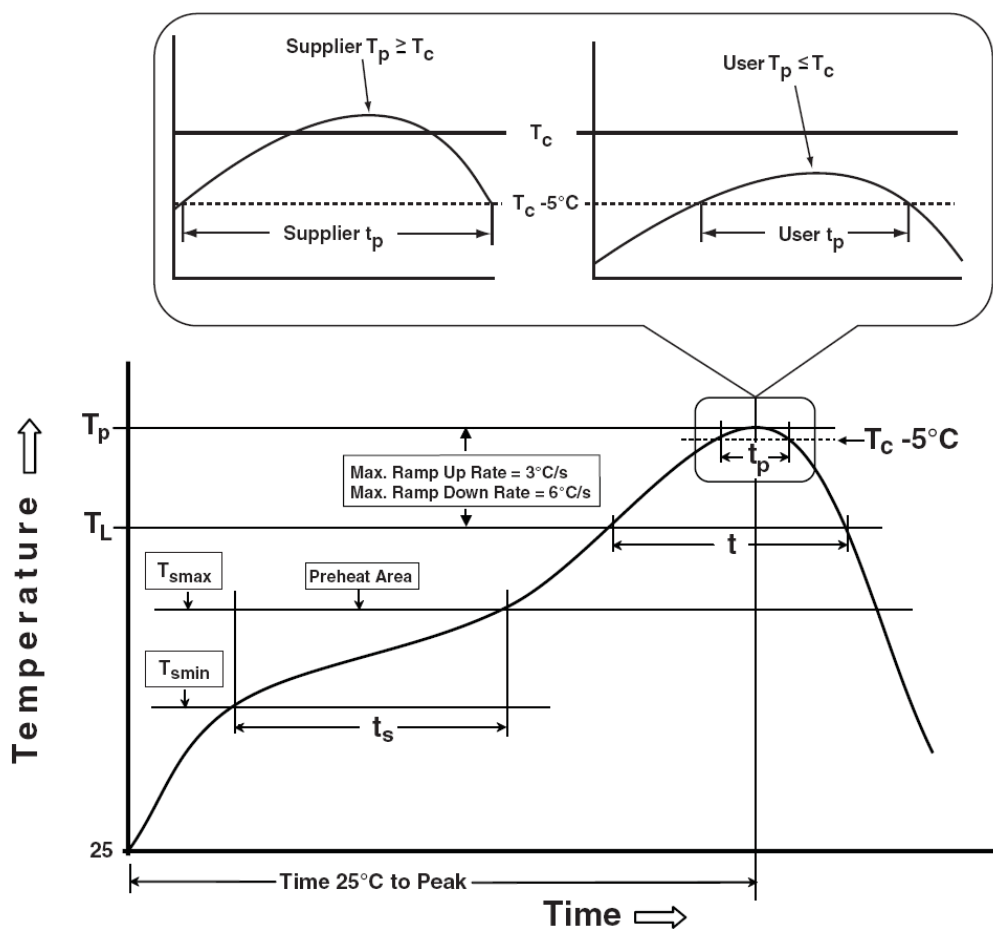
(mm)

Taping Direction Information

SOT-23N



Classification Profile



Disclaimer

Sinopower Semiconductor, Inc. (hereinafter “Sinopower”) has been making great efforts to development high quality and better performance products to satisfy all customers’ needs. However, a product may fail to meet customer’s expectation or malfunction for various situations.

All information which is shown in the datasheet is based on Sinopower’s research and development result, therefore, Sinopower shall reserve the right to adjust the content and monitor the production.

In order to unify the quality and performance, Sinopower has been following JEDEC while defines assembly rule. Notwithstanding all the suppliers basically follow the rule for each product, different processes may cause slightly different results.

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Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T_{smin})	100 °C	150 °C
Temperature max (T_{smax})	150 °C	200 °C
Time (T_{smin} to T_{smax}) (t_s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T_{smax} to T_p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L)	183 °C	217 °C
Time at liquidous (t_L)	60-150 seconds	60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_p)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum.		
** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.		

Table 1. SnPb Eutectic Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HOLT	JESD-22, A108	1000 Hrs, Bias @ 125°C
PCT	JESD-22, A102	168 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	500 Cycles, -65°C~150°C

Customer Service

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